

CMXD4448
SURFACE MOUNT
TRIPLE ISOLATED
HIGH SPEED
SILICON SWITCHING DIODES



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DESCRIPTION:

The CENTRAL SEMICONDUCTOR CMXD4448 type contains three (3) Isolated High Speed Silicon Switching Diodes, manufactured by the epitaxial planar process, epoxy molded in a SUPERmini™ surface mount package, and designed for applications requiring high speed switching.

MARKING CODE: X48

MAXIMUM RATINGS: (T_A=25°C)

Continuous Reverse Voltage
 Peak Repetitive Reverse Voltage
 Continuous Forward Current
 Peak Repetitive Forward Current
 Peak Forward Surge Current, t_p=1.0μs
 Peak Forward Surge Current, t_p=1.0s
 Power Dissipation
 Operating and Storage Junction Temperature
 Thermal Resistance

SYMBOL

V_R 75
 V_{RRM} 100
 I_F 250
 I_{FRM} 500
 I_{FSM} 4.0
 I_{FSM} 1.0
 P_D 350
 T_J, T_{stg} -65 to +150
 Θ_{JA} 357

UNITS

V
 V
 mA
 mA
 A
 A
 mW
 °C
 °C/W

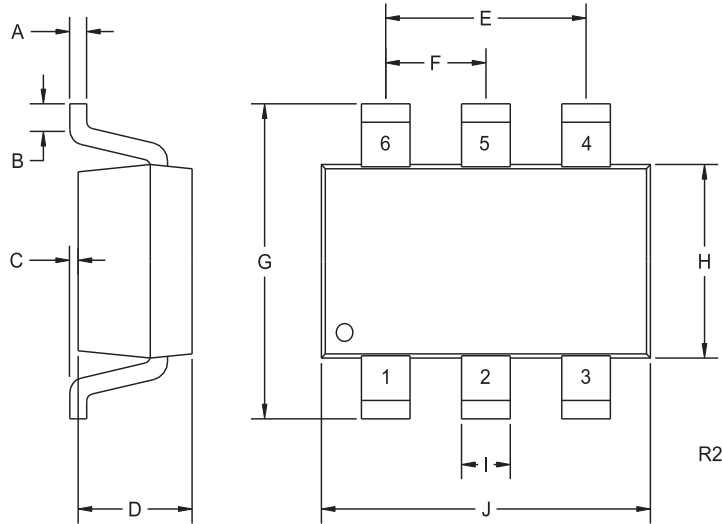
ELECTRICAL CHARACTERISTICS PER DIODE: (T_A=25°C unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
I _R	V _R =20V		25	nA
BV _R	I _R =5.0μA	75		V
BV _R	I _R =100μA	100		V
V _F	I _F =100mA		1.0	V
C _T	V _R =0, f=1.0MHz		4.0	pF
t _{rr}	I _R =I _F =10mA, I _{rr} =1.0mA, R _L =100Ω		4.0	ns

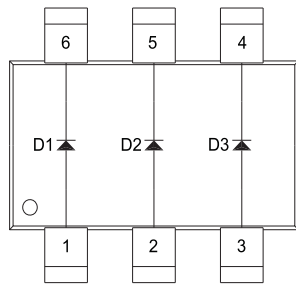
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SOT-26 CASE - MECHANICAL OUTLINE



PIN CONFIGURATION



SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.004	0.007	0.11	0.19
B	0.016	-	0.40	-
C	-	0.004	-	0.10
D	0.039	0.047	1.00	1.20
E	0.074	0.075	1.88	1.92
F	0.037	0.038	0.93	0.97
G	0.102	0.118	2.60	3.00
H	0.059	0.067	1.50	1.70
I	0.016		0.41	
J	0.110	0.118	2.80	3.00

SOT-26 (REV: R2)

LEAD CODE:

- 1) Anode D1
- 2) Anode D2
- 3) Anode D3
- 4) Cathode D3
- 5) Cathode D2
- 6) Cathode D1

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R5 (12-February 2010)